

Inclined Rotary Plasma Enhanced Chemical Deposition Pecvd Tube Furnace Machine

Item Number: KT-PE16



Introduction

Advanced PECVD Tube Furnace for precise thin film deposition. Uniform heating, RF plasma source, customizable gas control. Ideal for semiconductor research.

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Furnace model	PE-1600-60
Max. temperature	1600°C
Constant work temperature	1550°C
Furnace tube material	High purity Al ₂ O ₃ tube
Furnace tube diameter	60mm
Heating zone length	2x300mm
Chamber material	Japan alumina fiber
Heating element	Molybdenum Disilicide
Heating rate	0-10°C/min
Thermal couple	B type
Temperature controller	Digital PID controller/Touch screen PID controller
Temperature control accuracy	±1°C
RF Plasma unit	
Output Power	5 -500W adjustable with ± 1% stability
RF frequency	13.56 MHz ±0.005% stability
Reflection Power	350W max.
Matching	Automatic
Noise	
Cooling	Air cooling.
Gas precise control unit	
Flow meter	MFC mass flow meter
Gas channels	4 channels
Flow rate	MFC1: 0-55SCCM O ₂ MFC2: 0-20SCCMCH ₄ MFC3: 0- 100SCCM H ₂ MFC4: 0-500 SCCM N ₂
Linearity	±0.5% F.S.

Repeatability	±0.2% F.S.
Pipe line and valve	Stainless steel
Maximum Operating Pressure	0.45MPa
Flow meter controller	Digital Knob controller/Touch screen controller
Standard vacuum unit(Optional)	
Vacuum pump	Rotary vane vacuum pump
Pump flow rate	4L/S
Vacuum suction port	KF25
Vacuum gauge	Pirani/Resistance silicon vacuum gauge
Rated vacuum pressure	10Pa
High vacuum unit(Optional)	
Vacuum pump	Rotary vane pump+Molecular pump
Pump flow rate	4L/S+110L/S
Vacuum suction port	KF25
Vacuum gauge	Compound vacuum gauge
Rated vacuum pressure	6x10 ⁻⁵ Pa
Above specifications and setups can be customized	

No.	Description	Quantity
1	Furnace	1
2	Quartz tube	1
3	Vacuum flange	2
4	Tube thermal block	2
5	Tube thermal block hook	1
6	Heat resistant glove	1
7	RF plasma source	1
8	Precise gas control	1
9	Vacuum unit	1
10	Operation manual	1